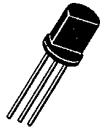


Signal Transistors

2N2926

J-29-15

Silicon Transistors



TO-98

The GE/RCA 2N2926 is a planar passivated NPN silicon transistor intended for general purpose applications. The planar passivated construction assures excellent device stability

and life. This high performance, high value device is made possible by advanced manufacturing techniques.

This type is supplied in JEDEC TO-98 package.

Devices in TO-98 package are supplied with and without seating flange (see Dimensional Outline).

MAXIMUM RATINGS, Absolute-Maximum Values:

COLLECTOR TO EMITTER VOLTAGE (V_{CE0})	25 V
EMITTER TO BASE VOLTAGE (V_{EB0})	5 V
COLLECTOR TO BASE VOLTAGE (V_{CB0})	25 V
CONTINUOUS COLLECTOR CURRENT (I_C) (Note 1)	100 mA
TOTAL POWER DISSIPATION ($T_A \leq 25^\circ\text{C}$) (P_T) (Note 2)	200 mW
TOTAL POWER DISSIPATION ($T_A \leq 55^\circ\text{C}$) (P_T) (Note 2)	120 mW
OPERATING TEMPERATURE (T_J)	-55° to +100°C
STORAGE TEMPERATURE (T_{STG})	-55° to +150°C
LEAD TEMPERATURE, 1/16" \pm 1/32" (1.58mm \pm 0.8mm) from case for 10s max (T_L)	+260°C

NOTES:

1. Determined from power limitations due to saturation voltage at this current.
2. Derate 2.67mW/°C increase in ambient temperature above 25°C.

File Number **2052**

Signal Transistors

T-29-15

2N2926

ELECTRICAL CHARACTERISTICS, At Ambient Temperature (T_A) = 25°C Unless Otherwise Specified

CHARACTERISTICS	SYMBOL	LIMITS			UNITS
		MIN.	TYP.	MAX.	
Collector Cutoff Current ($V_{CB} = 18V$)	I_{CBO}	—	—	0.5	μA
($V_{CB} = 18V, T_A = 100^\circ C$)		—	—	15	
Emitter Cutoff Current ($V_{EB} = 5V$)		I_{EBO}	—	—	
Small-Signal Forward Current Transfer Ratio ($V_{CE} = 10V, I_C = 2mA, f = 1Hz$)	h_{fe}	35		470	—
Input Impedance ($V_{CE} = 10V, I_C = 2mA, f = 1Hz$)	h_{ib}	—	15	—	Ω
Gain Bandwidth Product ($I_C = 2mA, V_{CB} = 5V$)	f_T	—	120	—	MHz
Collector Capacitance ($V_{CB} = 10V, I_E = 0, f = 1MHz$)	C_{ob}	4.5	7	10	pF

TERMINAL CONNECTIONS

- Lead 1 - Emitter
- Lead 2 - Collector
- Lead 3 - Base